

ABSTRACT OF THE DISCLOSURE

A susceptor is formed with a cavity having a tapered surface and a receiving surface. The gradient α of the tapered surface with respect to the receiving surface is set to at least 5° and less than 30° , so that a semiconductor wafer received by the susceptor

5 can be located on the receiving surface through the tapered surface while the semiconductor wafer can be protected against excess stress also when the surface of the wafer abruptly thermally expands due to flashlight irradiation and can be prevented from cracking in thermal processing. Thus provided are a thermal processing susceptor and a thermal processing apparatus capable of preventing a substrate from cracking in thermal

10 processing.